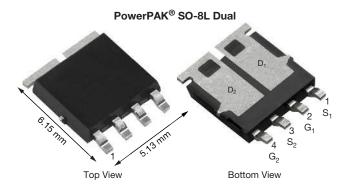
SQJ968EP



Vishay Siliconix

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0336
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0444
I _D (A) per leg	23.5
Configuration	Dual
Package	PowerPAK SO-8L

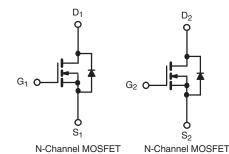


FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	v
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current ^a	T _C = 25 °C	1	23.5	
	T _C = 125 °C	I _D	13.5	
Continuous Source Current (Diode Conduction) ^a		I _S	23	А
Pulsed Drain Current ^b	I _{DM}	72		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	9	
Single Pulse Avalanche Energy		E _{AS}	4	mJ
Maria a Dana Diasia ta ta b	T _C = 25 °C	Р	42	w
Maximum Power Dissipation ^b	$T_{\rm C} = 125 ^{\circ}{\rm C}$	P _D	14	vv
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Tempera	ature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	3.5	C/W

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static					•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	$V_{GS} = 0 V, I_{D} = 250 \mu A$		-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	V 2.0 2.5 V - ±100 nA		
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		$V_{GS} = 10 V$	I _D = 4.8 A	-	0.0280	0.0336	
Durin Source On State Desistance a	Б	$V_{GS} = 10 V$	I _D = 4.8 A, T _J = 125 °C	-	-	0.0900	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.8 A, T _J = 175 °C	-	-	0.1430	Ω
		$V_{GS} = 4.5 V$	I _D = 4.2 A	-	0.0370	0.0444	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 4.8 A		-	16	-	S
Dynamic ^b		•		•		•	
Input Capacitance	C _{iss}		V _{DS} = 30 V, f = 1 MHz	-	571	714	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	98	123	
Reverse Transfer Capacitance	C _{rss}			-	38	48	
Total Gate Charge ^c	Qg			-	12.3	18.5	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 4.5 \text{ A}$	-	1.9	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	2.6	-	
Gate Resistance	R _g	f = 1 MHz		1.3	-	6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8	12	
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 30 \; V, \; R_L = 30 \; \Omega \\ I_D \cong 1 \; A, \; V_GEN = 10 \; V, \; R_g = 1 \; \Omega \end{array}$		-	9	13.5	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	19.5	29	
Fall Time ^c	t _f		-	6.5	10		
Source-Drain Diode Ratings and Chara	acteristics ^b	·			•		
Pulsed Current ^a	I _{SM}			-	-	32	Α
Forward Voltage	V _{SD}	I _F = 3.1 A, V _{GS} = 0 V		-	0.8	1.1	V

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

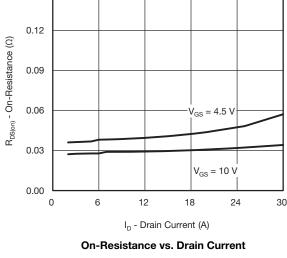
c. Independent of operating temperature.

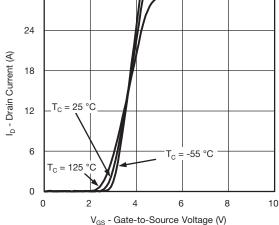
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

T_C = 125 °C T_C -55 °C 0 3 4 5 0 1 2 1 2 V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics** 1000

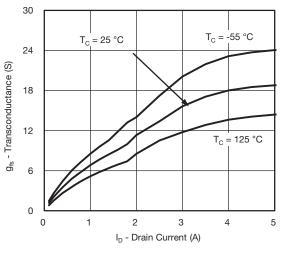
$V_{GS} = 3 V$ 0 8 10 6 0 2 V_{DS} - Drain-to-Source Voltage (V) **Output Characteristics** 30

30

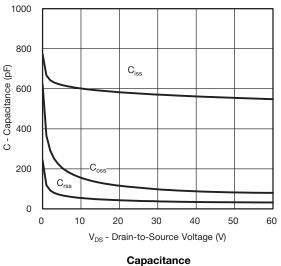








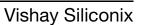




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Document Number: 62817

For technical questions, contact: automostechsupport@vishay.com





V_{GS} = 10 V thru 5 V

 $V_{GS} = 4 V$

4

°C $\Gamma_{\rm C} = 25$

24

18

12

6

0

10.0

8.0

6.0

4.0

2.0

0.0

0.15

0

l_D - Drain Current (A)

0

2

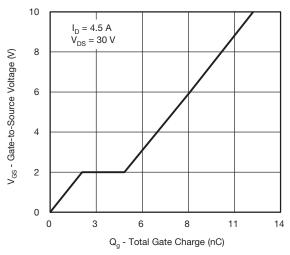
I_D - Drain Current (A)

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted) 30

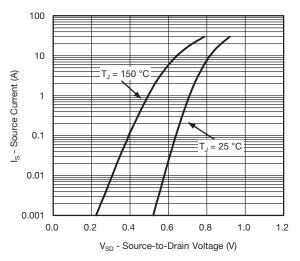
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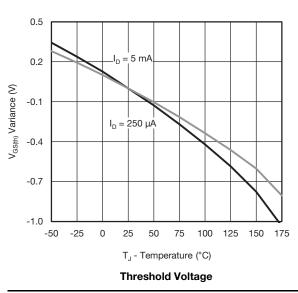
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

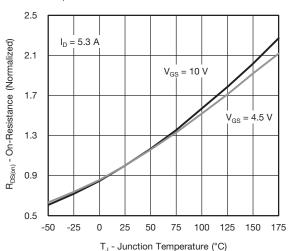




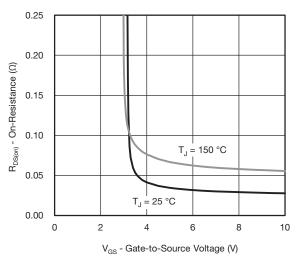


Source Drain Diode Forward Voltage

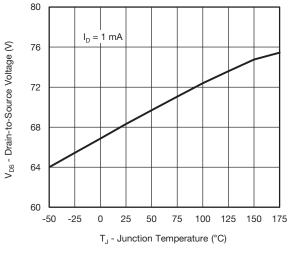




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

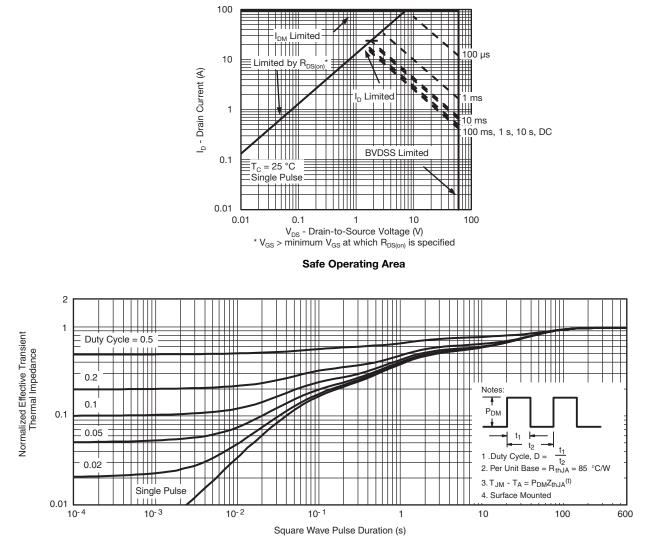
S16-1227-Rev. C, 20-Jun-16

Document Number: 62817

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



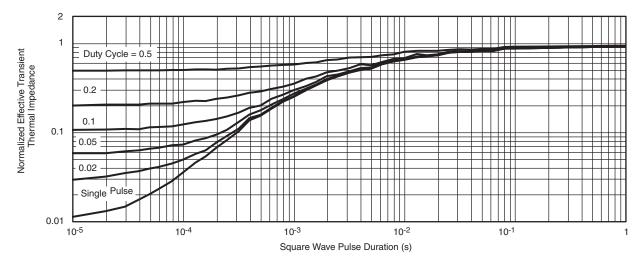
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62817.



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REVISION HISTORY^a

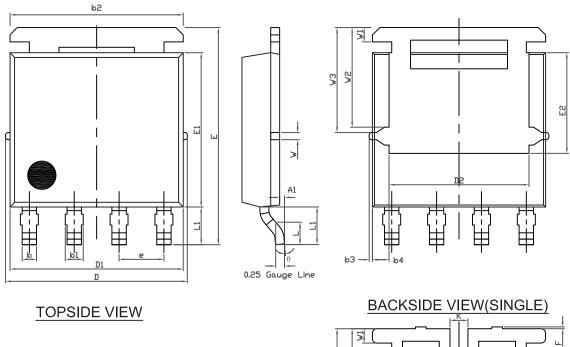
NEVISION	moroni	
REVISION	DATE	DESCRIPTION OF CHANGE
В	04-Aug-15	Revised R _g minimum limit
С	14-Jun-16	• I _D and P _D corrected

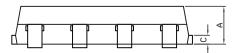
Note

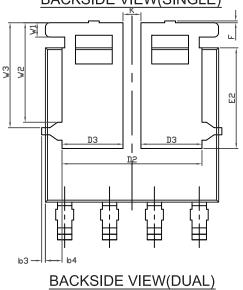
a. As of April 2014



PowerPAK[®] SO-8L Case Outline 2







Package Information



Vishay Siliconix

DIM.		MILLIMETERS			INCHES		
DINI.	MIN. NOM. MAX.			MIN. NOM. MAX			
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3	2.96			0.117			
q	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



Vishay

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